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an active layer, provided between said n-type and p-type nitride semiconductor layers, having a multi-quantum well structure having a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-y}\text{N}$ ,  $0 \leq y < 1$ ; and  
a p-type contact layer formed of a p-type GaN provided over said first p-type clad layer.

64. (New) A nitride semiconductor light-emitting device comprising:

an n-type layer comprising an n-type GaN or and n-type nitride semiconductor containing indium and gallium;  
a first p-type clad layer comprising a p-type nitride semiconductor containing indium and gallium;  
an active layer, provided between said n-type and p-type nitride semiconductor layers, having a multi-quantum well structure having a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-y}\text{N}$ ,  $0 \leq y < 1$ ;  
a second p-type clad layer made of a p-type nitride semiconductor provided over said first p-type clad layer; and  
a p-type contact layer formed of a p-type GaN provided over said second p-type clad layer.

65. (New) The device according to claim 69, wherein said p-type clad layer includes a first p-type layer comprising a p-type nitride semiconductor containing no aluminum provided over said active layer, and a second p-type layer comprising a p-type

nitride semiconductor containing aluminum and gallium provided over said first p-type layer.

66. (New) The device according to claim 71, further comprising a p-type contact layer formed of a p-type GaN provided over said second p-type clad layer, and an n-type contact layer formed of an n-type GaN and over which said second n-type clad layer is provided.

67. (New) A nitride semiconductor light emitting diode device comprising:  
a substrate;  
an n-type layer formed of n-type GaN provided over said substrate;  
an active layer having a multi-quantum well structure including a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ , said active layer being provided over said n-type layer;  
a first p-type layer formed of p-type AlGaN provided over said active layer; and  
a second p-type layer formed of p-type GaN provided over said first p-type layer.

68. (New) A nitride semiconductor light-emitting device comprising:  
an n-type nitride semiconductor layer, said n-type nitride semiconductor layer comprising an n-type GaN or an n-type nitride semiconductor containing indium and gallium;

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a p-type nitride semiconductor layer including a p-type clad layer, said p-type clad layer comprising a p-type nitride semiconductor containing aluminum and gallium and having a thickness within a range of 10 angstroms to 1.0  $\mu\text{m}$ ; and

an active layer, provided between said n-type and p-type nitride semiconductor layers, having a multi-quantum well structure having a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and a barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ .

69. (New) A nitride semiconductor/light-emitting device comprising:  
a first n-type clad layer comprising an n-type nitride semiconductor not containing aluminum;  
a p-type clad layer comprising a p-type nitride semiconductor and having a surface region, said surface region comprising a p-type nitride semiconductor containing aluminum and gallium; and

an active layer, provided between said first n-type clad layer and said p-type clad layer, having a multi-quantum well structure including a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and a barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ .

70. (New) A nitride semiconductor light-emitting device comprising:  
an active layer having a multi-quantum well structure having a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and a

barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ ;

a negative electrode;

a positive electrode;

an n-type GaN contact layer in electrical contact with said negative electrode;

a p-type GaN contact layer in electrical contact with said positive electrode; and

a p-type clad layer provided between said active layer and said p-type GaN contact layer, said p-type clad layer comprising a p-type nitride semiconductor containing aluminum and gallium.

71. (New) A nitride semiconductor light-emitting device comprising:

a first n-type clad layer comprising an n-type nitride semiconductor containing indium and gallium;

a first p-type clad layer comprising a p-type nitride semiconductor containing indium and gallium;

an active layer provided between said first n-type and p-type clad layers and having a multi-quantum well structure including a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and a barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ ;

a second n-type clad layer comprising an n-type nitride semiconductor containing aluminum and gallium, said second n-type clad layer having a larger band gap than said first n-type clad layer, said first n-type clad layer being provided over said second n-type clad layer; and